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**PATENTS**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**Applicant: Meikei Leong, et al.**  
**Application No: 10/647395**  
**Patent No: 6,815,278**

**Docket: 16527**  
**Dated: April 8, 2005**

**Issued: November 9, 2004**

**For: ULTRA-THIN SILICON-ON-INSULATOR AND  
STRAINED-SILICON-DIRECT-ON-  
INSULATOR WITH HYBIRD CRYSTAL  
ORIENTATIONS**

**Commissioner of Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450**

**REQUEST FOR CERTIFICATE OF CORRECTION**

**Sir:**

**It appearing that errors have been introduced in the course of  
printing the Patent issued in the above application,  
it is respectfully requested that the Commissioner issue a Certificate of Correction  
in the following respects:**

**Column 12, Line 21 "stained" should read – strained –**

**Column 11, Line 54 "the method of claim wherein" should read -- the  
method of claim 1 wherein --**

**Column 12, Line 30 "Insert missing paragraph"**

**–forming an insulator layer on the structure and bonding the insulator to a  
handling wafer; selectively removing the carrier wafer, first semiconductor  
layer and the second  
semiconductor layer to expose the second graded SiGe alloy; and --**

**It is further noted that additional errors typographical in nature are incorporated into the printed specification, but are believed to be satisfactorily clear in the context and accordingly it is simply requested that this paper be made of record in the file for such clarification as may be appropriate. They are as follows:**

**Column 3, Line 44 "stained" should read -- strained --**

**Column 3, Line 66 "stained" should read -- strained --**

**Column 12, Line 9 "nFET the (100) suface" should read -- nFET on the (100) surface --**

**Respectfully submitted,**

**Leslie S. Szivos  
Reg. No. 39,394**

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UNITED STATES PATENT AND TRADEMARK OFFICE  
CERTIFICATE OF CORRECTION

PATENT NO : 6,815,278

DATED : November 9, 2004

INVENTOR(S) : Melkel leong, et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 12, Line 21 "stained" should read -- strained --

Column 11, Line 54 "the method of claim wherein" should read -- the method of claim 1 wherein --

Column 12, Line 30 "Insert missing paragraph"

--forming an insulator layer on the structure and bonding the insulator to a handling wafer; selectively removing the carrier wafer, first semiconductor layer and the second semiconductor layer to expose the second graded SiGe alloy; and --

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